IN THE CLAIMS:

Claims 1-16 (canceled)

17. (New) A method of producing a silicon ingot, comprising:

producing a silicon ingot having growth defects under the following conditions:

(1) $1.15 \leq (G1_{edge}/G1_{center}) \leq 1.25$;

(2) $0.5 < (\text{OSF ring inner diameter/crystal diameter}) < 1.06 \times (G1_{edge}/G1_{center})^{-0.2}$

where

$G1_{center}$ is a temperature gradient in the axial direction at the crystal center in the temperature region from the solid-liquid interface temperature to approximately 1350°C and $G1_{edge}$ is a temperature gradient in the axial direction at the crystal edge in the temperature region from the solid-liquid interface temperature to approximately 1350°C; and

cutting the wafer from portions, of the produced ingot, in which the inner diameter of the OSF ring is at least 1/2 the crystal diameter.

18. (New) A method of producing a silicon ingot, comprising the steps of:

controlling the $G1_{edge}$ and the $G1_{center}$ of the ingot so that:

(1) $1.15 \leq (G1_{edge}/G1_{center}) \leq 1.25$;

(2) $0.5 < (\text{OSF ring inner diameter/crystal diameter}) < 1.06 \times (G1_{edge}/G1_{center})^{-0.2}$

where

$G1_{center}$ is a temperature gradient in the axial direction at the crystal center in the temperature region from the solid-liquid interface temperature to approximately 1350°C and

$G1_{edge}$ is a temperature gradient in the axial direction at the crystal edge in the temperature region from the solid-liquid interface temperature to approximately 1350°C; and

cutting the wafer from portions, of the produced ingot, in which the inner diameter of the OSF ring is at least 1/2 the crystal diameter.